复合沟道 MOSFET

ELM54539CWSA-N

■概要

ELM54539CWSA-N 是低输入电容、低工作电压、低导通电阻的大电流 MOSFET。同时内藏有 N 沟道和 P 沟道的复合产品。

■特点

N 沟道	P 沟道
・Vds=30V	・Vds=-30V
・Id=5.4A	・Id=-5.4A
・Rds(on) = 36mΩ(Vgs=10V)	・Rds(on) = 62mΩ(Vgs=-10V)
・Rds(on) = 46mΩ(Vgs=4.5V)	・Rds(on) = 90mΩ(Vgs=-4.5V)

■绝对最大额定值

如没有特别注明时, Ta=25℃

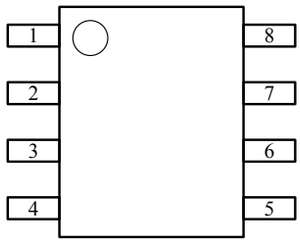
项目		记号	N 沟道 (最大值)	P 沟道 (最大值)	单位
漏极 – 源极电压		Vds	30	-30	V
栅极 – 源极电压		Vgs	± 20	± 20	V
漏极电流 (定常) (Tj=150℃)	Ta=25℃	Id	5.4	-5.4	A
	Ta=70℃		4.0	-4.2	
漏极电流 (脉冲)		Idm	20	-30	A
容许功耗	Tc=25℃	Pd	2.8	2.8	W
	Tc=70℃		1.8	1.8	
结合部温度		Tj	150	150	℃
保存温度范围		Tstg	-55 ~ 150	-55 ~ 150	℃

■热特性

项目	记号	沟道	典型值	最大值	单位
最大结合部 – 环境热阻	Rθja	N		62.5	℃/W
最大结合部 – 环境热阻	Rθja	P		62.5	℃/W

■引脚配置图

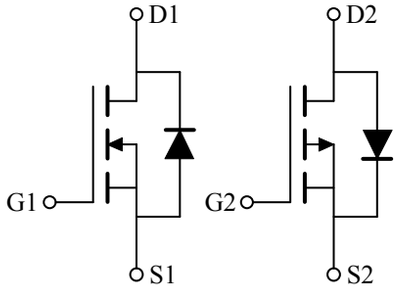
SOP-8(俯视图)



引脚编号	引脚名称
1	SOURCE1
2	GATE1
3	SOURCE2
4	GATE2
5	DRAIN2
6	DRAIN2
7	DRAIN1
8	DRAIN1

■电路图

・N 沟道　　・P 沟道

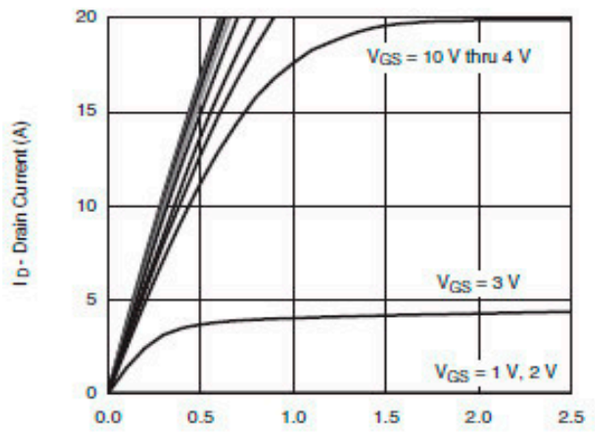


■电特性 (N 沟道)

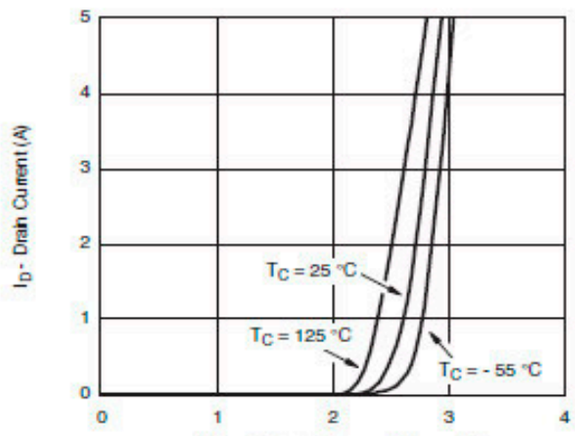
如没有特别注明时, Ta=25℃

项目	记号	条件		最小值	典型值	最大值	单位
静态特性							
漏极 – 源极击穿电压	BVdss	Id=250μA, Vgs=0V		30			V
栅极接地时漏极电流	Idss	Vds=24V, Vgs=0V				1	μA
			Ta=85℃			30	
栅极漏电电流	Igss	Vds=0V, Vgs= ± 20V				± 100	nA
栅极阈值电压	Vgs(th)	Vds=Vgs, Id=250μA		1.3		2.1	V
导通时漏极电流	Id(on)	Vgs=4.5V, Vds≧5V		10			A
漏极 – 源极导通电阻	Rds(on)	Vgs=10V, Id=5.0A			30	36	mΩ
		Vgs=4.5V, Id=4.7A			40	46	
正向跨导	Gfs	Vds=15V, Id=5.2A			13		S
二极管正向压降	Vsd	Is=1.6A, Vgs=0V			0.8	1.3	V
寄生二极管最大连续电流	Is					1.5	A
动态特性							
输入电容	Ciss	Vgs=0V, Vds=20V, f=1MHz			700		pF
输出电容	Coss				75		pF
反馈电容	Crss				45		pF
开关特性							
总栅极电荷	Qg	Vgs=4.5V, Vds=20V, Id≡5.2A			8.0	12.0	nC
栅极 – 源极电荷	Qgs				1.6		nC
栅极 – 漏极电荷	Qgd				2.4		nC
导通延迟时间	td(on)	Vgs=10V, Vds=15V, Id≡1.0A RL=15Ω, Rgen=6Ω			8	12	ns
导通上升时间	tr				12	18	ns
关闭延迟时间	td(off)				28	40	ns
关闭下降时间	tf				10	18	ns

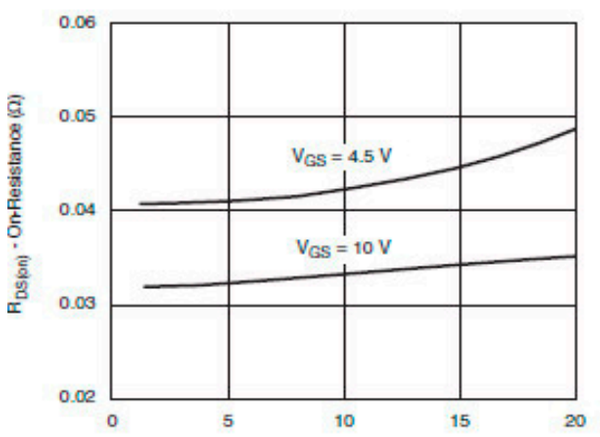
■标准特性曲线 (N 沟道)



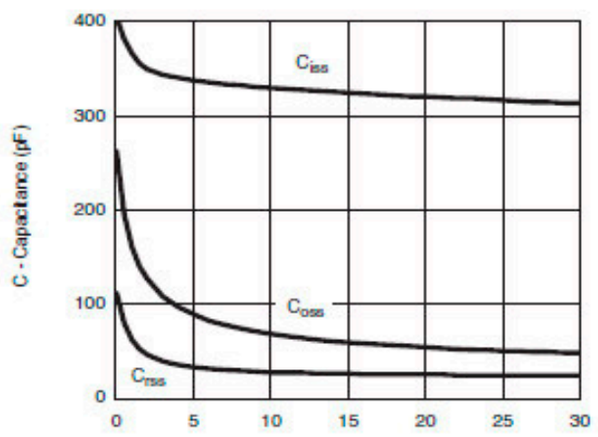
Output Characteristics



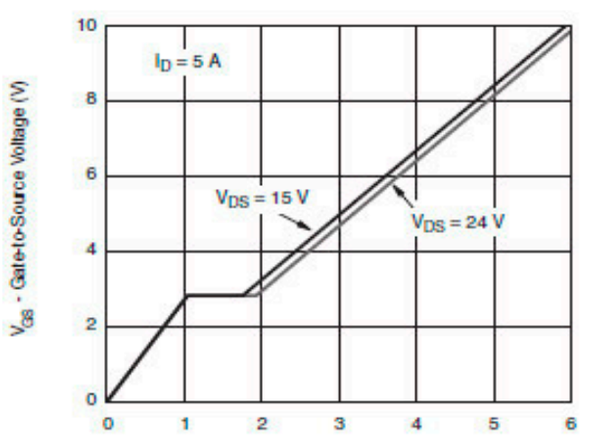
Transfer Characteristics



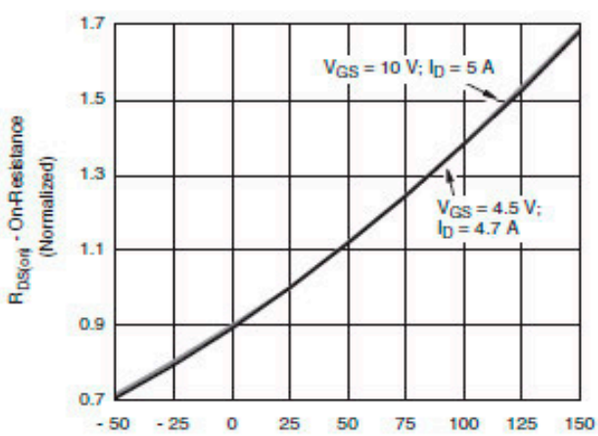
On-Resistance vs. Drain Current



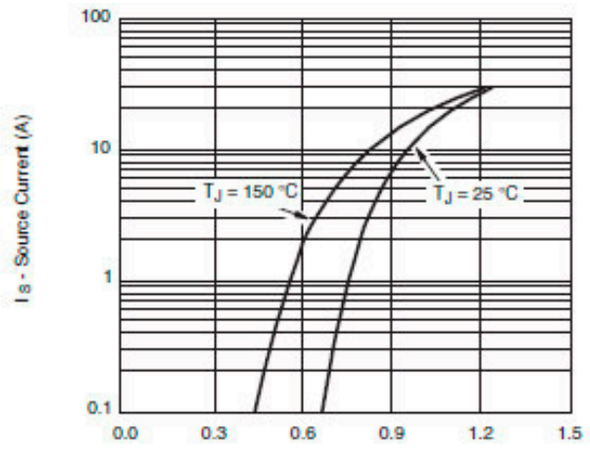
Capacitance



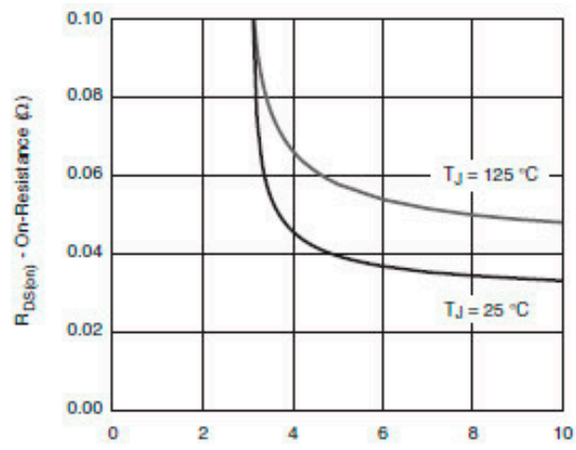
Gate Charge



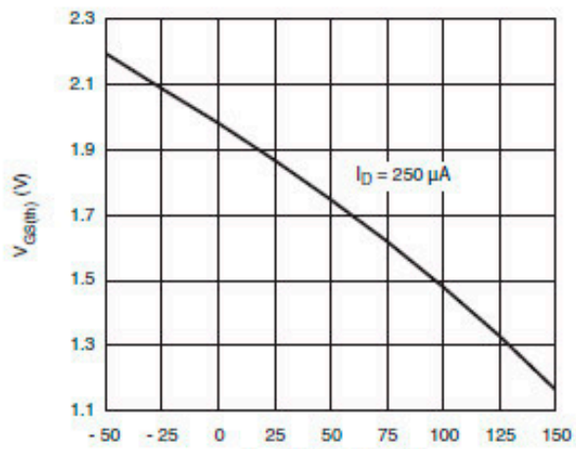
On-Resistance vs. Junction Temperature



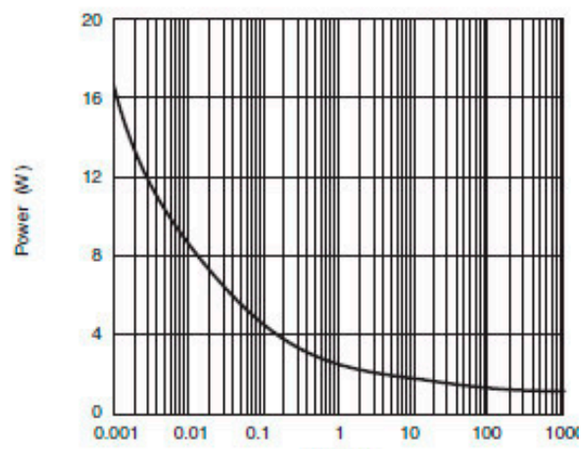
Source-Drain Diode Forward Voltage



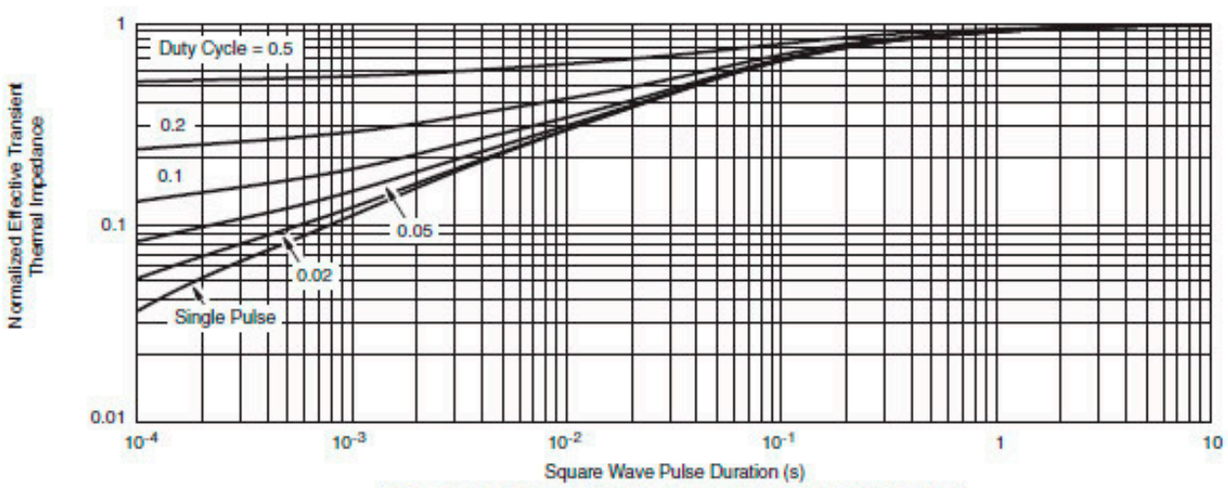
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Foot

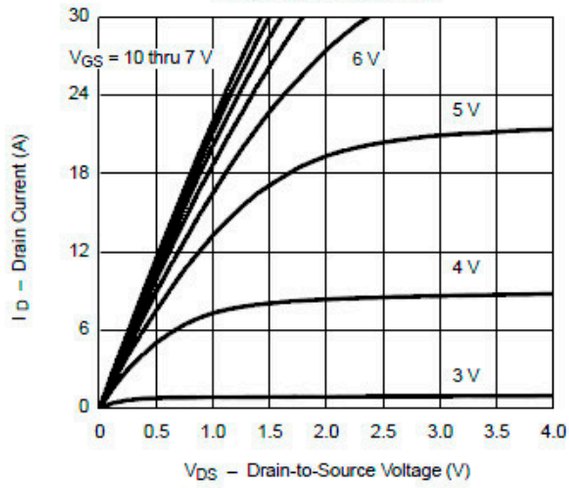
■电特性 (P 沟道)

如没有特别注明时, Ta=25℃

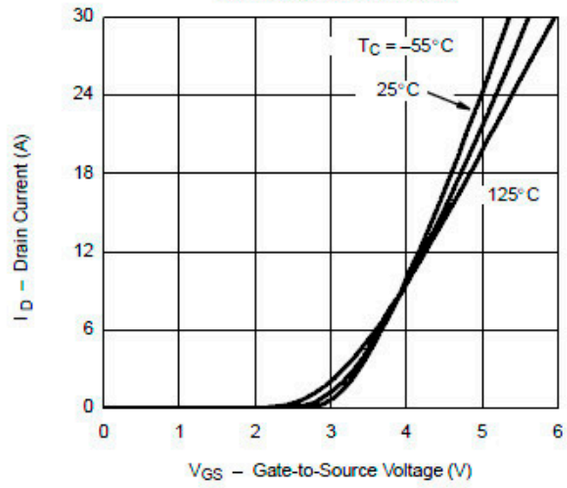
项目	记号	条件		最小值	典型值	最大值	单位
静态特性							
漏极 – 源极击穿电压	BVdss	Id=–250μA, Vgs=0V		–30			V
栅极接地时漏极电流	Idss	Vds=–24V, Vgs=0V				–1	μA
			Ta=85℃			–30	
栅极漏电电流	Igss	Vds=0V, Vgs= ± 20V				± 100	nA
栅极阈值电压	Vgs(th)	Vds=Vgs, Id=–250μA		–1.0		–2.5	V
导通时漏极电流	Id(on)	Vgs=–10V, Vds≧–5V		–25			A
漏极 – 源极导通电阻	Rds(on)	Vgs=–10V, Id=–5.4A			52	62	mΩ
		Vgs=–4.5V, Id=–4.2A			70	90	
正向跨导	Gfs	Vds=–10V, Id=–4.9A			10		S
二极管正向压降	Vsd	Is=–1.7A, Vgs=0V			–0.8	–1.3	V
寄生二极管最大连续电流	Is					–1.7	A
动态特性							
输入电容	Ciss	Vgs=0V, Vds=–15V, f=1MHz			500		pF
输出电容	Coss				100		pF
反馈电容	Crss				55		pF
开关特性							
总栅极电荷	Qg	Vgs=–10V, Vds=–15V, Id≡–5A			10.0	18.0	nC
栅极 – 源极电荷	Qgs				1.6		nC
栅极 – 漏极电荷	Qgd				3.0		nC
导通延迟时间	td(on)	Vgs=–10V, Vds=–15V Id≡–1.0A, RL=15Ω Rgen=6Ω			8	18	ns
导通上升时间	tr				8	18	ns
关闭延迟时间	td(off)				25	50	ns
关闭下降时间	tf				25	35	ns

■标准特性曲线 (P 沟道)

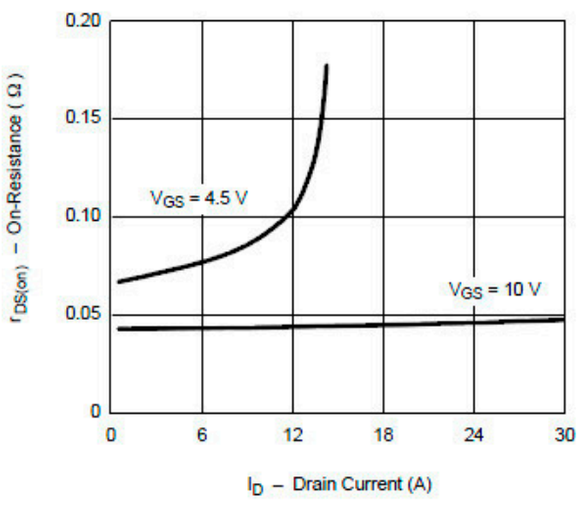
Output Characteristics



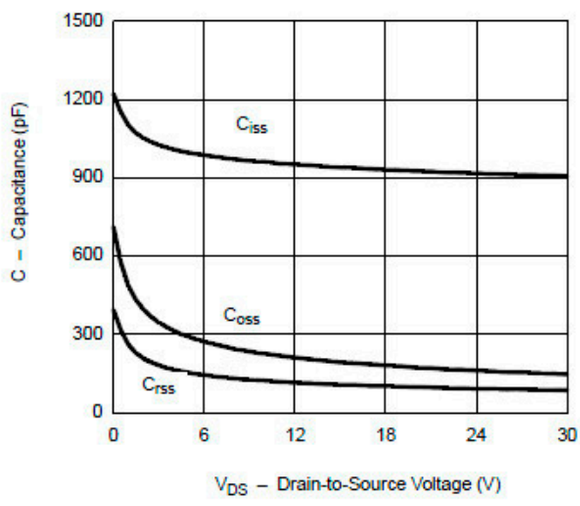
Transfer Characteristics



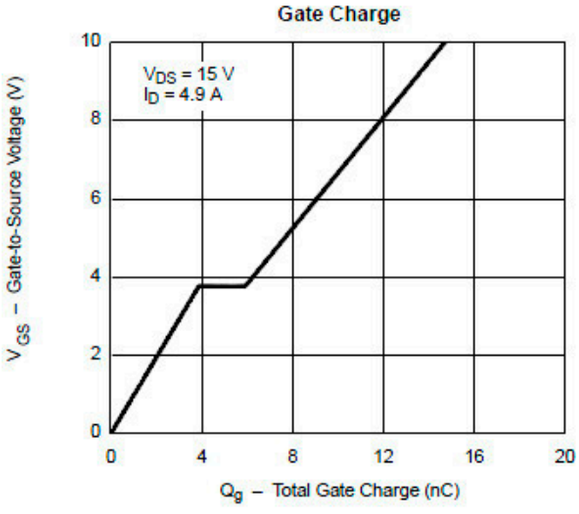
On-Resistance vs. Drain Current



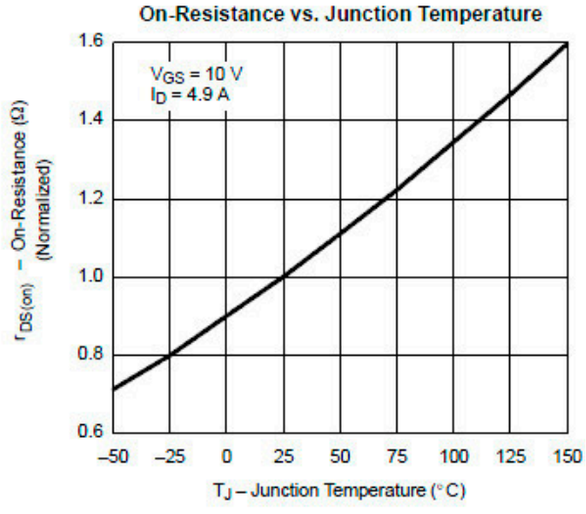
Capacitance



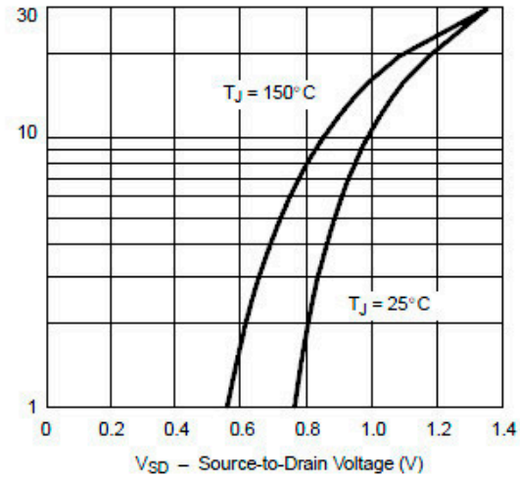
Gate Charge



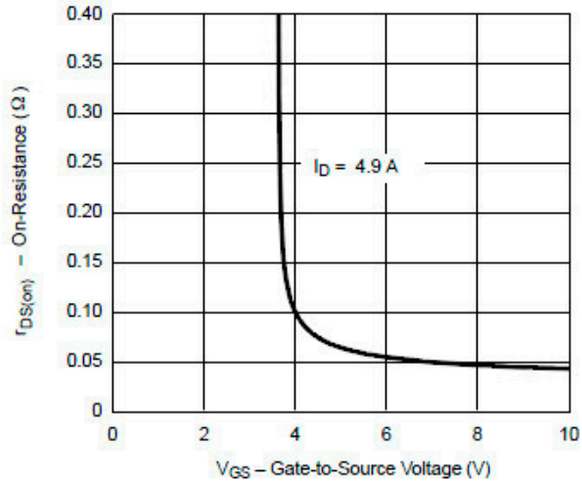
On-Resistance vs. Junction Temperature



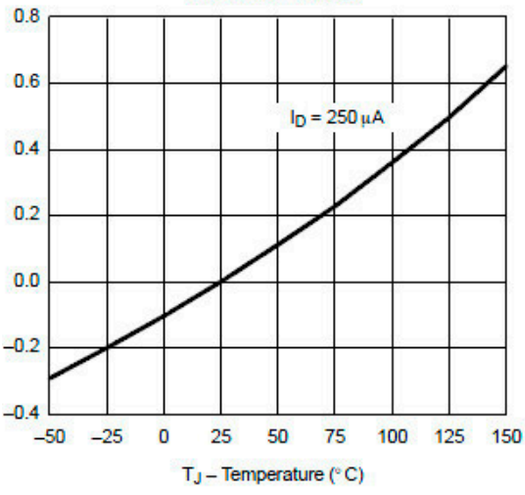
Source-Drain Diode Forward Voltage



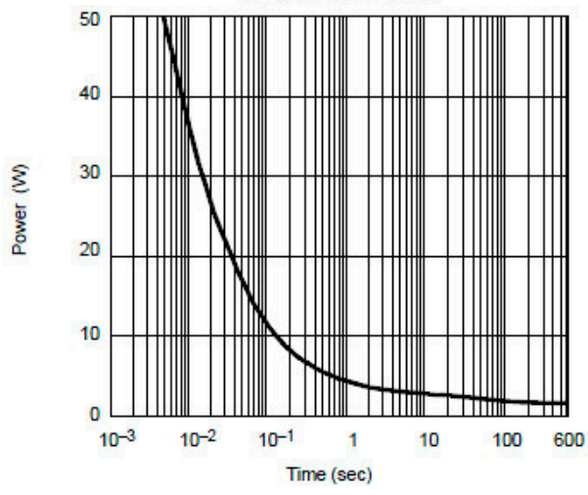
On-Resistance vs. Gate-to-Source Voltage



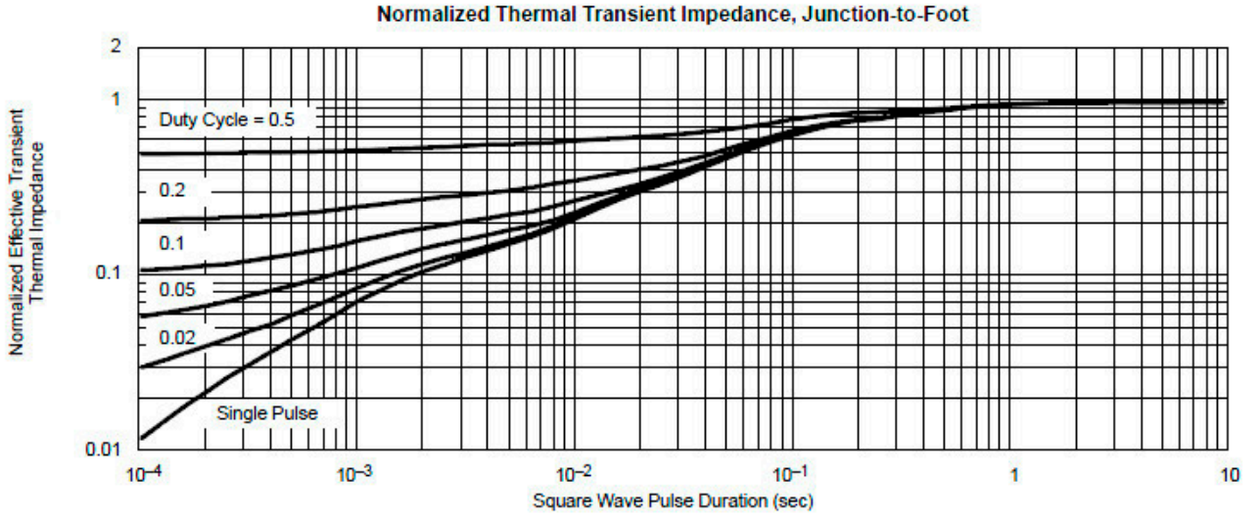
Threshold Voltage



Single Pulse Power

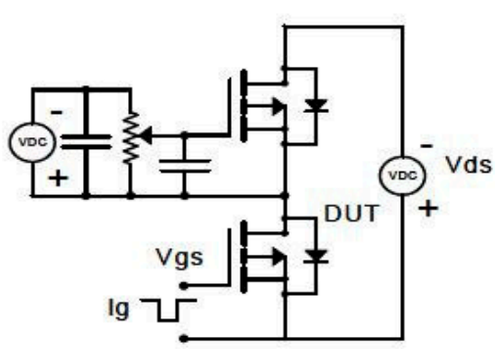


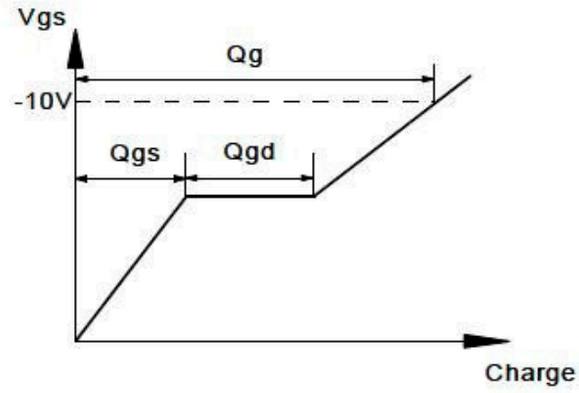
Normalized Thermal Transient Impedance, Junction-to-Foot



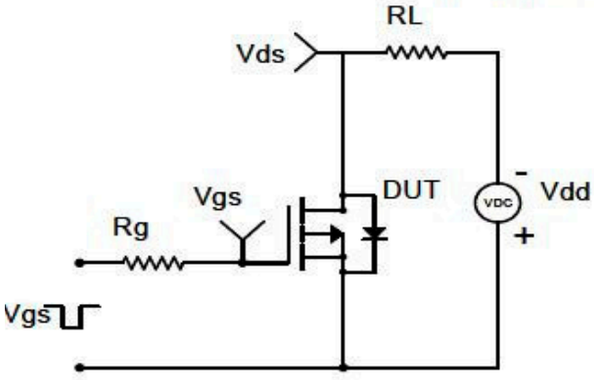
■测试电路和波形

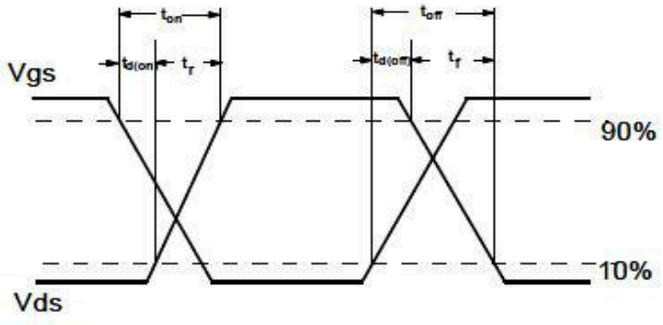
Gate Charge Test Circuit & Waveform





Resistive Switching Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms